

MOSFETs Silicon N-Channel MOS (π-MOSVIII)

# TK7J90E

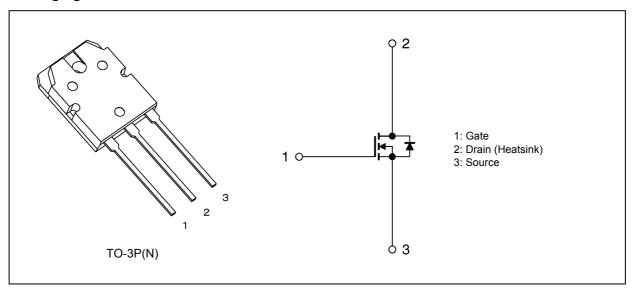
#### 1. Applications

· Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 1.6 \Omega$  (typ.)
- (2) Low leakage current :  $I_{DSS} = 10 \mu A \text{ (max)} \text{ (V}_{DS} = 720 \text{ V)}$
- (3) Enhancement mode:  $V_{th}$  = 2.5 to 4.0 V ( $V_{DS}$  = 10 V,  $I_{D}$  = 0.7 mA)

#### 3. Packaging and Internal Circuit





# 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

| Characteristics                | Symbol                  | Rating           | Unit       |       |
|--------------------------------|-------------------------|------------------|------------|-------|
| Drain-source voltage           |                         | $V_{DSS}$        | 900        | V     |
| Gate-source voltage            |                         | V <sub>GSS</sub> | ±30        |       |
| Drain current (DC)             | (Note 1)                | I <sub>D</sub>   | 7          | Α     |
| Drain current (pulsed)         | (Note 1)                | I <sub>DP</sub>  | 21         |       |
| Power dissipation              | (T <sub>c</sub> = 25°C) | $P_{D}$          | 200        | W     |
| Single-pulse avalanche energy  | (Note 2)                | E <sub>AS</sub>  | 235        | mJ    |
| Avalanche current              |                         | I <sub>AR</sub>  | 7          | Α     |
| Reverse drain current (DC)     | (Note 1)                | I <sub>DR</sub>  | 7          |       |
| Reverse drain current (pulsed) | (Note 1)                | I <sub>DRP</sub> | 21         |       |
| Channel temperature            |                         | T <sub>ch</sub>  | 150        | °C    |
| Storage temperature            |                         | T <sub>stg</sub> | -55 to 150 |       |
| Mounting torque                |                         | TOR              | 0.8        | N · m |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

| Characteristics                       | Symbol                | Max   | Unit |
|---------------------------------------|-----------------------|-------|------|
| Channel-to-case thermal resistance    | R <sub>th(ch-c)</sub> | 0.625 | °C/W |
| Channel-to-ambient thermal resistance | R <sub>th(ch-a)</sub> | 50    | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 8.8 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 7 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

# 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                | Symbol               | Test Condition                                    | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|------|-----|------|
| Gate leakage current           | I <sub>GSS</sub>     | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$ | _   | _    | ±1  | μΑ   |
| Drain cut-off current          | I <sub>DSS</sub>     | V <sub>DS</sub> = 720 V, V <sub>GS</sub> = 0 V    | _   | _    | 10  |      |
| Drain-source breakdown voltage | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V     | 900 | _    | _   | V    |
| Gate threshold voltage         | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.7 mA   | 2.5 | _    | 4.0 |      |
| Drain-source on-resistance     | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3.5 A    | _   | 1.6  | 2.0 | Ω    |

# 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub> | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz | _   | 1350 | _   | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> |  | _   | 10   | _   |      |
| Output capacitance             | C <sub>oss</sub> |  | _   | 110  | _   |      |
| Gate resistance                | r <sub>g</sub>   | V <sub>DS</sub> = OPEN, f = 1 MHz                        | _   | 4.0  | _   | Ω    |
| Switching time (rise time)     | t <sub>r</sub>   | See Fig. 6.2.1.  | _   | 20   | _   | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>  |  | _   | 55   | _   |      |
| Switching time (fall time)     | t <sub>f</sub>   |  | _   | 15   | _   |      |
| Switching time (turn-off time) | t <sub>off</sub> | ]  | _   | 85   | _   |      |
| MOSFET dv/dt ruggedness        | dv/dt            | V <sub>DD</sub> = 0 to 400 V, I <sub>D</sub> = 7 A       | 20  | _    |     | V/ns |

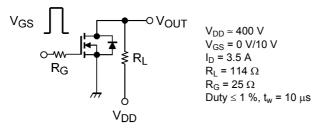


Fig. 6.2.1 Switching Time Test Circuit

# 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                                 | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 7 \text{ A}$ | _   | 32   | _   | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> |  | _   | 10   | _   |      |
| Gate-drain charge                               | Q <sub>gd</sub>  |  | _   | 12   | _   |      |

# 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics               | Symbol          | Test Condition                               | Min | Тур. | Max  | Unit |
|-------------------------------|-----------------|--|-----|------|------|------|
| Diode forward voltage         | $V_{DSF}$       | I <sub>DR</sub> = 7 A, V <sub>GS</sub> = 0 V | _   | _    | -1.7 | V    |
| Reverse recovery time         | t <sub>rr</sub> | I <sub>DR</sub> = 7 A, V <sub>GS</sub> = 0 V | _   | 1100 | _    | ns   |
| Reverse recovery charge       | Q <sub>rr</sub> | -dI <sub>DR</sub> /dt = 100 A/μs             | _   | 8    | _    | μС   |
| Peak reverse recovery current | I <sub>rr</sub> |  | _   | 18   | _    | Α    |



# 7. Marking (Note)

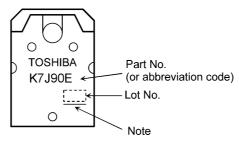


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

#### 8. Characteristics Curves (Note)

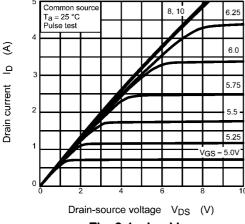


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

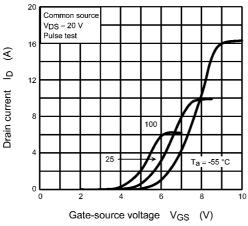


Fig. 8.3  $I_D - V_{GS}$ 

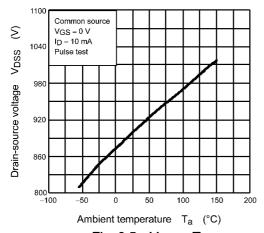


Fig. 8.5 V<sub>DSS</sub> - T<sub>a</sub>

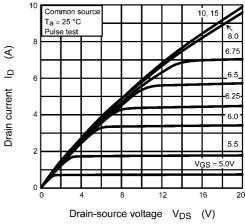


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

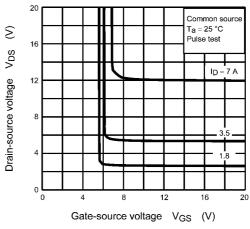


Fig. 8.4  $V_{DS}$  -  $V_{GS}$ 

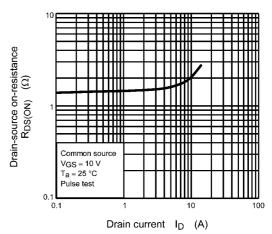


Fig. 8.6  $R_{DS(ON)}$  -  $I_D$ 

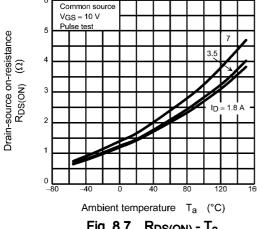


Fig. 8.7 R<sub>DS(ON)</sub> - T<sub>a</sub>

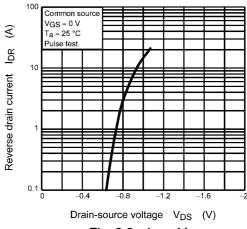


Fig. 8.8 I<sub>DR</sub> - V<sub>DS</sub>

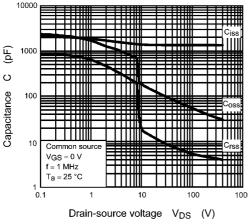


Fig. 8.9 C - V<sub>DS</sub>

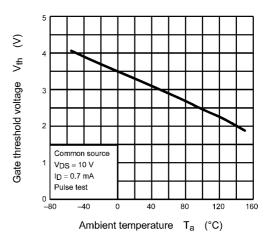


Fig. 8.10 V<sub>th</sub> - T<sub>a</sub>

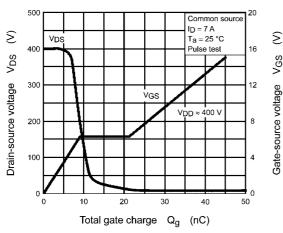


Fig. 8.11 Dynamic Input/Output Characteristics

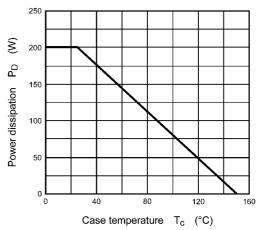


Fig. 8.12 PD - Tc (Guaranteed Maximum)

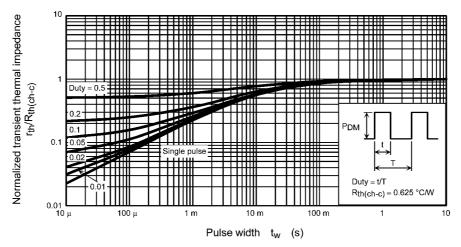


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

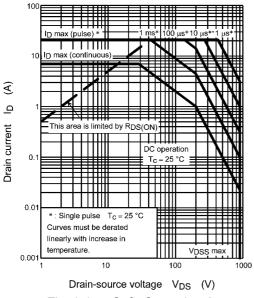


Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

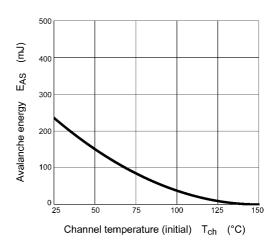


Fig. 8.15 E<sub>AS</sub> - T<sub>ch</sub> (Guaranteed Maximum)

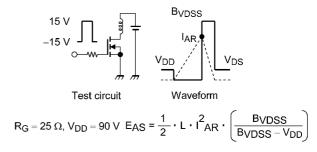


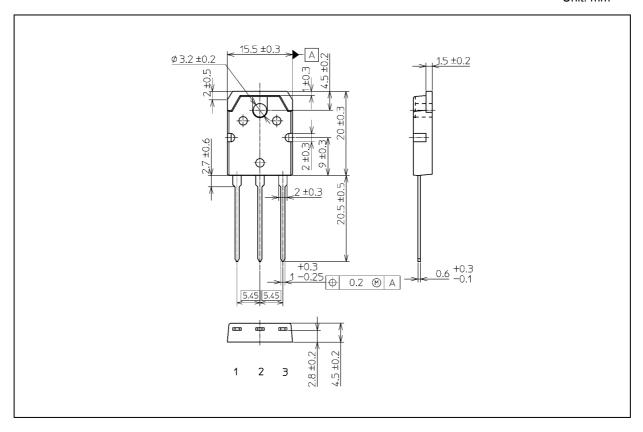
Fig. 8.16 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



# **Package Dimensions**

Unit: mm



Weight: 4.6 g (typ.)

|                    | Package Name(s) |
|--------------------|-----------------|
| JEITA: SC-65       |                 |
| TOSHIBA: 2-16C1S   |                 |
| Nickname: TO-3P(N) |                 |



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